

Super Fast Recovery Diode

RF2L6S

●Series

Standard Fast Recovery

●Applications

General rectification

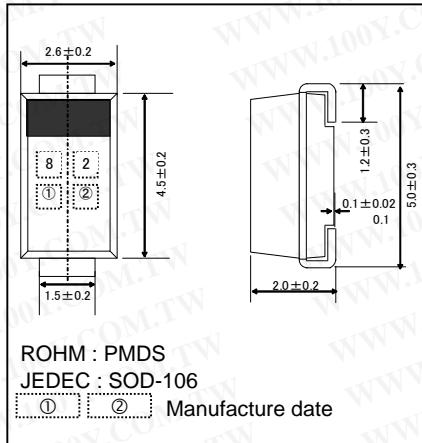
●Features

- 1) Small power mold type. (PMDS)
- 2) High switching speed
- 3) Low forward voltage

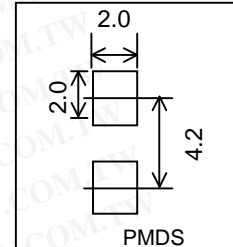
●Construction

Silicon epitaxial planar

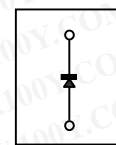
●Dimensions (Unit : mm)



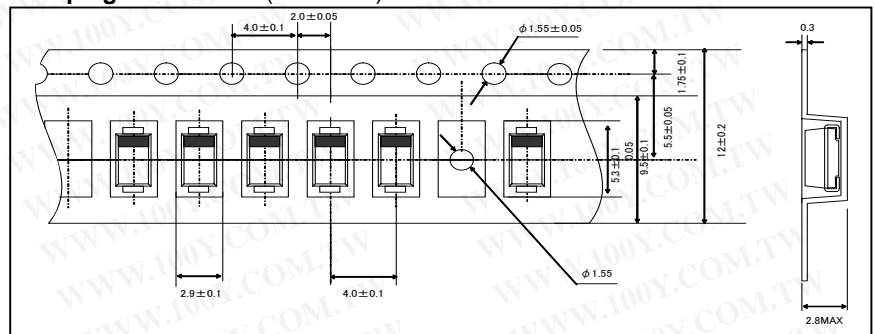
●Land size figure (Unit : mm)



●Structure



●Taping dimensions (Unit : mm)



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●Absolute maximum ratings (Tl=25°C)

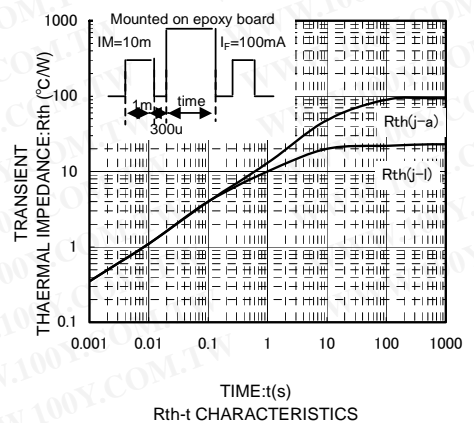
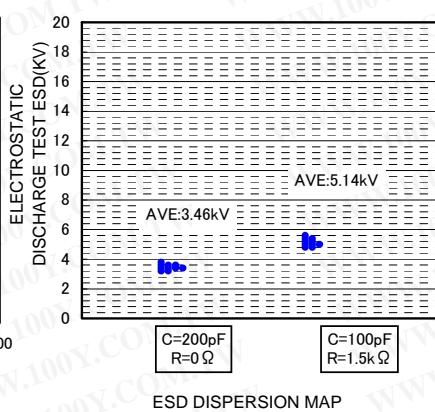
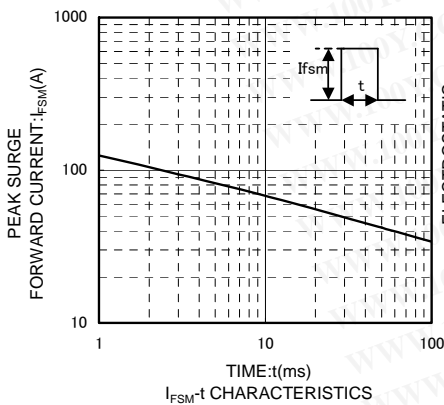
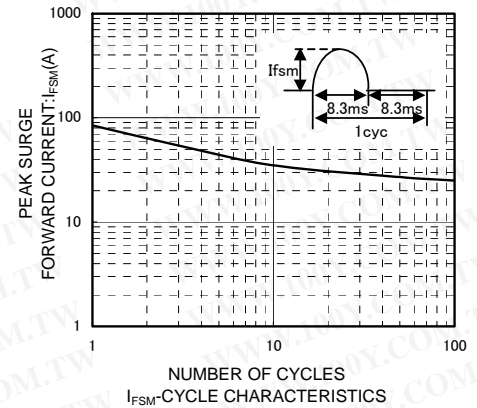
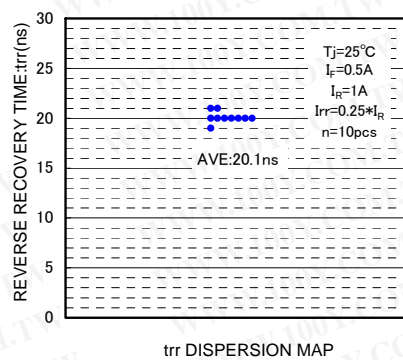
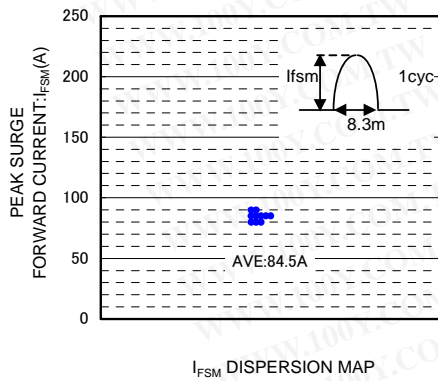
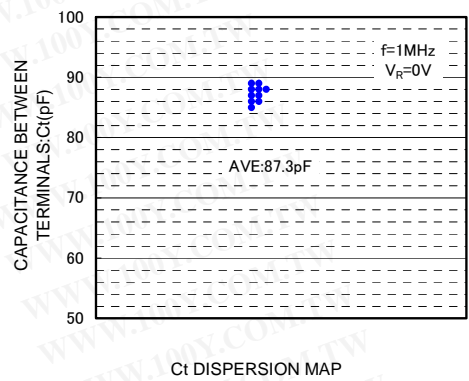
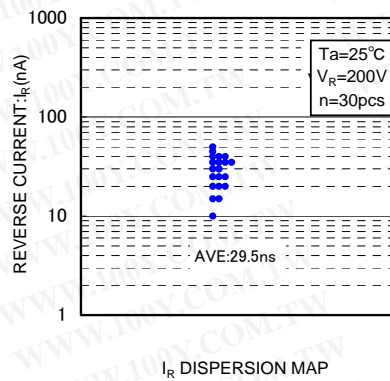
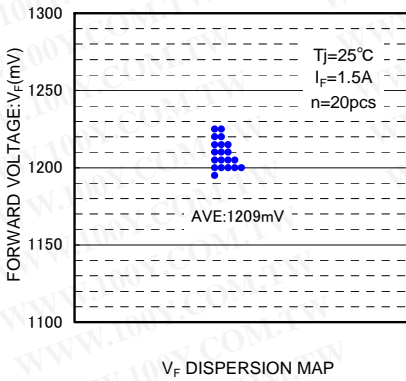
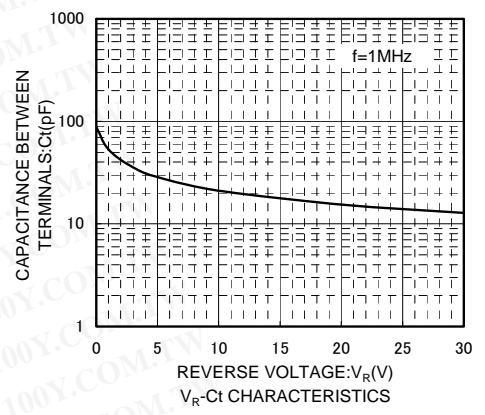
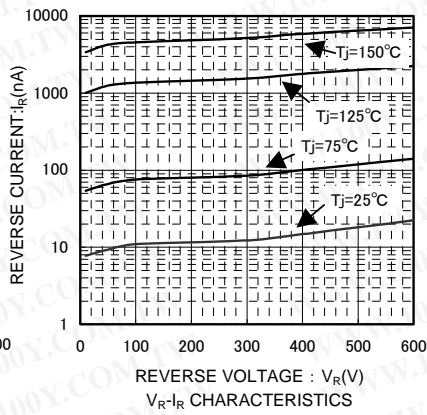
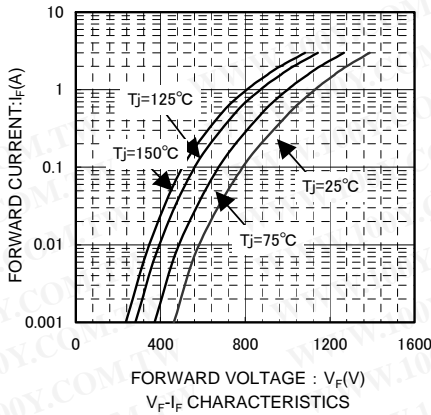
Parameter	Symbol	Limits	Unit
Repetitive peak Reverse voltage	V_{RM}	600	V
Reverse voltage	V_R	600	V
Average rectified forward current(*1)	I_o	1.5	A
Forward current surge peak (60Hz, 1cyc, Tj=25°C)	I_{FSM}	40	A
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

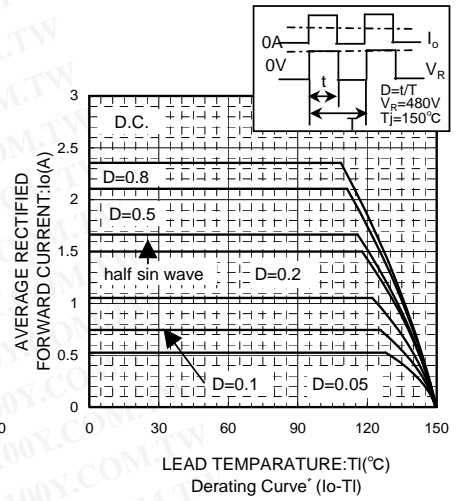
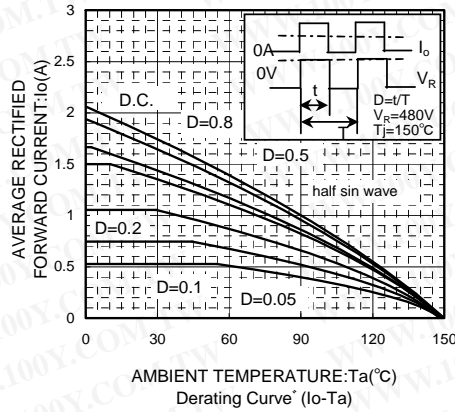
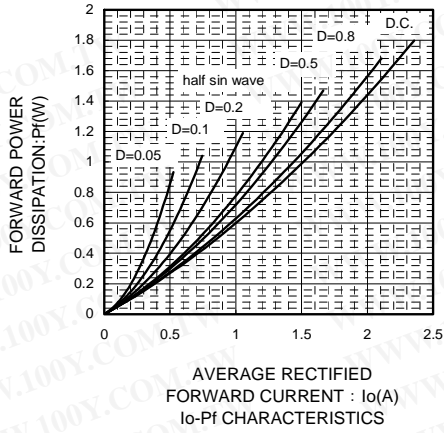
(*1) Half sinwave on the Glass epoxy substrate (size : 50mmx50mm), Tc=90°CMax.

●Electrical characteristics (Tj=25°C)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward voltage	V_F	$I_F=1.5A$	-	1.25	1.55	V
Reverse current	I_R	$V_R=600V$	-	0.03	10	μA
Reverse recovery time	trr	$I_F=0.5A, I_R=1A, I_{rr}=0.25 \times I_R$	-	20	35	ns
Thermal Resistance	Rth (j-l)	junction to lead	-	-	23	°C/W

●Electrical characteristics curves





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